

ABSTRACT OF THE DISCLOSURE

Provided is a nonvolatile memory that realizes a high-speed verify operation. During verify writing/erasing, the writing/erasing and reading are performed at the same time. As to a circuit that performs a verify operation, for instance, there is obtained a construction where the output from a sense amplifier (102) that performs reading is connected to a switch which switches an operation voltage applied to a memory cell in accordance with a verify signal S_v , and the verify operation is finished concurrently with having the verify signal S_v switched. By obtaining such circuit construction and simultaneously performing writing/erasing and reading, it becomes possible to perform high-speed verify writing/erasing.